

Session Program

Nov 14 - 16, 2012

21st RD50 Workshop (CERN)

Defect and Material Characterization

CERN

6-2-024 on 14th & 15th Nov. 222-R-001 on 16th Nov.

Wed, November 14

2:00 PM

Defect and Material Characterization

Session | **Location:** CERN, 6-2-024 on 14th & 15th Nov. 222-R-001 on 16th Nov. | **Convener:** Michael Moll

2:00 – 2:20 PM

Electronic properties of vacancy aggregates in n-type silicon for particle detectors

Speaker

Prof. Pawel Kaminski

2:20 – 2:40 PM

Radiation damage in n-type silicon after electron irradiation with energies between 1.5 MeV and 15 MeV

Speaker

Roxana Radu

2:40 – 3:00 PM

RADIATION DEFECT TRANSFORMATIONS UNDER ANNEALING OF P-TYPE SILICON

Speaker

Dr Leonid Makarenko

3:00 – 3:20 PM

Evolution of pulsed current and of carrier lifetime characteristics in Si structures during 25 MeV neutrons irradiation using a spallator type source

Speaker

Dr Eugenijus Gaubas

3:20 – 3:40 PM

The free carrier transport properties in proton and neutron irradiated Si(Ge)

Speaker

Prof. Juozas Vaitkus

3:40 – 4:10 PM

Coffee

4:10 – 4:30 PM

Charge carrier detrapping in irradiated silicon sensors after microsecond laser pulses

Speaker

Markus Gabrysch

4:30 – 4:50 PM

Measurements on 800 MeV proton irradiated diodes (moved to Thursday morning!)

Speaker

Alexandra Junkes

4:50 – 5:10 PM

MOS Capacitor Displacement Damage Dose (DDD) Dosimeter

Speaker

Dr Fco.Rogelio Palomo Pinto

5:10 - 5:20 PM

New proton irradiation facility in Ankara

Speaker

Bilge Demirkoz

5:20 - 5:50 PM

Discussion Session: Materials and Defects

Speaker

Michael Moll

5:50 PM